COURSE OBJECTIVES:

EC/EE-202

1. To understand semiconductor basics like semiconductor material, its types, concepts of Drift current, diffusion current.

ELECTRONIC DEVICES AND CIRCUITS

- 2. To understand the principle of operation and characteristics of Diode, Tunnel Diode and Rectifiers.
- 3. To understand the principle of operation and characteristics of BiPolar Junction Transistor.
- 4. To analyze the transistor biasing and thermal stabilization of transistor, operation and characteristics of JFET.
- 5. To understand the principle of operation and characteristics of MOSFET.

COURSE OUTCOMES:

After successful completion of the course, the students are able to

R.V.R. & J.C. College of Engineering (Autonomous), Guntur-522019, A.P.

- understand PN junction diode current components and characteristics, Zener diode and its electrical characteristics, Rectifiers and capacitor filters, Working and characteristics of BJT, JFET, MOS capacitor and MOSFET.
- Analyze the rectifiers, filters and transistor biasing circuits for the given set of specifications.
- 3. design biasing techniques such as fixed bias, collector to base bias and self-bias for the given specifications.
- 4. solve numerical and analytical problems in PN junction diode, Zener diode voltage regulator, rectifiers, filters, BJT, JFET and MOSFET.
- 5. select the appropriate mode of operation for modeling the behavior of PN junction diode, Zener diode, BJT, JFET, and MOSFET.

UNIT I

PN JUNCTION: Basic Structure of the PN Junction, Zero applied Bias, Reverse applied Bias, Non-Uniformly Doped Junctions, PN Junction Current, Generation-Recombination Currents, Junction Break Down, Zener diode as voltage regulator, Capacitances of The Diode. The Tunnel Diode.

UNIT II

BIPOLAR TRANSISTOR: The Bipolar Transistor Action, Minority Carrier Distribution, Low-Frequency Common-Base Current Gain, Nonideal Effects. Equivalent Circuit Models - Hybrid-Pi Model, Frequency limitations.

UNIT III

TRANSISTOR CHARACTERISTICS: Common Emitter, Common Base and Common Collector Characteristics, Photo Transistor.

TRANSISTOR BIASING: The Operating Point, Bias Stability, Biasing Techniques, Stabilization against variations in I_{co} , V_{BF} , β , Thermal Runaway.

UNIT IV

METAL-OXIDE-SEMICONDUCTOR FIELD-EFFECT TRANSISTOR: The Two Terminal MOS Structure, Capacitance-Voltage Characteristics, The Basic MOSFET Operation, Frequency limitations, Non-ideal Effects.

UNIT V

JUNCTION FIELD-EFFECT TRANSISTOR: JFET Concepts, The Device Characteristics, Non-ideal Effects, Equivalent Circuit and Frequency limitations.

RECTIFIERS: Half wave Rectifier and Full wave Rectifier with Capacitor filter.

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Text Book-2 (12)

Text Book-1 (12)

Text Book-1 (12)

Text Book-1, 2 (12)

Text Book-1 (12)

LEARNING RESOURCES:

TEXT BOOK(s):

- 1. Donald A. Neamen Semiconductor Physics and Devices, 3rd Edition, TMH, 2003.
- 2. Jacob Millman and Christos C. Halkias Integrated Electronics, TMH, 1972.

REFERENCE BOOK(s):

Ben G Streetman and Sanjay Banerjee, Solid State Electronic Devices, 5th Edition, 2000

WEB RESOURCES:

- 1. http://nptel.iitm.ac.in/courses/
- 2. http://www.deas.harvard.edu/courses/es154/